	Application No.	Applicant(s)
Notice of Allowability	10/623,691	YAMAUCHI, HIROYUKI
	Examiner	Art Unit
	Michael t Tran	2818
The MAILING DATE of this communication apperature All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIOF of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate comming GHTS. This application is	n this application. If not included unication will be mailed in due course. THIS
1. \boxtimes This communication is responsive to $\underline{communications\ filed}$	July 22, 2003.	
2. The allowed claim(s) is/are <u>1-24</u> .		
3. \boxtimes The drawings filed on <u>22 July 2003</u> are accepted by the Ex	aminer.	
 4. Acknowledgment is made of a claim for foreign priority ur a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority do International Bureau (PCT Rule 17.2(a)). * Certified copies not received: 	e been received. e been received in Application	on No
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	of this communication to file IENT of this application.	e a reply complying with the requirements
5. A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.		
6. CORRECTED DRAWINGS (as "replacement sheets") mus	st be submitted.	
(a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached		
1) hereto or 2) to Paper No./Mail Date		
(b) ☐ including changes required by the attached Examiner's Amendment / Comment or in the Office action of Paper No./Mail Date		
ldentifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).		
7. DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.		
 Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/O Paper No./Mail Date 072203 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material 	6. ☐ Interview S Paper No. 08), 7. ☐ Examiner's	oformal Patent Application (PTO-152) Summary (PTO-413), /Mail Date Amendment/Comment Statement of Reasons for Allowance
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DETAILED ACTION

1. In response to the Communication dated July 22, 2003, claims 1-24 are active in this application.

Foreign Priority

- 2. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)
- (d), which papers have been placed of record in the file.

Information Disclosure Statement

3. The information disclosure statement filed July 22, 2003 has been considered.

Allowable Subject Matter

- 4. Claims 1-24 are allowable over the prior art of record.
- 5. The following is an Examiner's statement of reasons for the indication of allowable subject matter: the prior art of records does not show (in addition to other elements in the claim) the following:
 - ❖ A potential supplied to non-selected word lines among the plurality of word lines by the word line potential supply source is set at a predetermined negative value, and a total of the absolute value of the precharge potential of the non-selected bit lines supplied by the precharge potential supply source and the absolute value of

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the potential of the non-selected word lines supplied by the word line potential supply source is a value less than the voltage of the power supply.

- A total of the absolute value of the precharge potential of the non-selected bit lines supplied by the precharge potential supply source and the absolute value of the potential of the non-selected word lines supplied by the word line potential supply source is set at a value less than the voltage of the power supply, and the absolute value of the potential of the non-selected word lines supplied by the word line potential supply source and the absolute value of the potential of the non-selected source lines supplied by the source potential supply source are roughly equal to each other.
- Wherein the decode circuit of the semiconductor memory has a transistor of which a source line is connected to the ground potential, the transistor being constructed of a transistor having a low threshold voltage of the same type as the transistor having a low threshold voltage included in the semiconductor circuit, and the word line drive circuit of the semiconductor memory has a pull-down transistor of which a source line for pulling down the potential of the word line is connected to a negative potential supply line, the pull-down transistor being constructed of a transistor having a high threshold voltage of the same type as the transistor having a high threshold voltage included in the semiconductor circuit.
- 6. Any comments considered necessary by applicant must be submitted no later than

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the payment of the Issue Fee and, to avoid processing delays, should preferably accompany the Issue Fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Michael T. Tran whose telephone number is (571) 272-1795.

8. Any inquiry of a general nature or relating to the status of this application should be directed to Group receptionist whose telephone number is (571) 272-1650.

Michael T. Tran

August 30, 2004